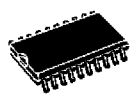
74VHC541

OCTAL BUS BUFFER WITH 3 STATE OUTPUTS (NON INVERTED)

- HIGH SPEED: t_{PD} = 3.6 ns (TYP.) at V_{CC} = 5V
- LOW POWER DISSIPATION: I_{CC} = 4 µA (MAX.) at T_A = 25 °C
- HIGH NOISE IMMUNITY: $V_{NIH} = V_{NIL}$ = 28% V_{CC} (MIN.)
- POWER DOWN PROTECTION ON INPUTS
- SYMMETRICAL OUTPUT IMPEDANCE: $|I_{OH}| = I_{OL}$ = 8 mA (MIN)
- BALANCED PROPAGATION DELAYS: $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 2V to 5.5V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 541
- IMPROVED LATCH-UP IMMUNITY
- LOW NOISE: V_{OLP} = 0.9V (Max.)



M
(Micro Package)

T
(TSSOP Package)

ORDER CODES :
74VHC541M 74VHC541T

DESCRIPTION

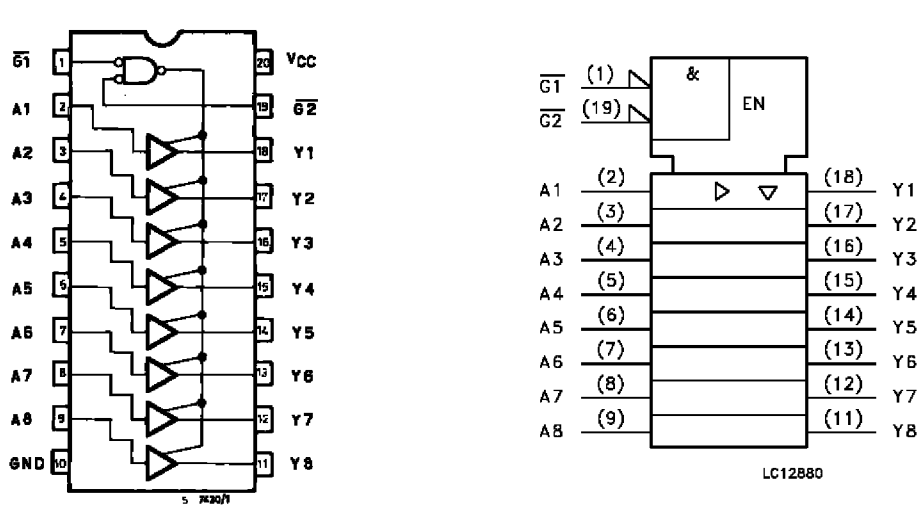
The VHC541 is an advanced high speed CMOS OCTAL BUS BUFFER (3-STATE) fabricated with sub-micron silicon gate and double-layer metal wiring C^2MOS technology.

The 3 STATE control gate operates as a two input AND such that if either $\overline{G1}$ and $\overline{G2}$ are high, all eight outputs are in the high impedance state. In order to enhance PC board layout, the AC541 offers a pinout having inputs and outputs on opposite sides of the package.

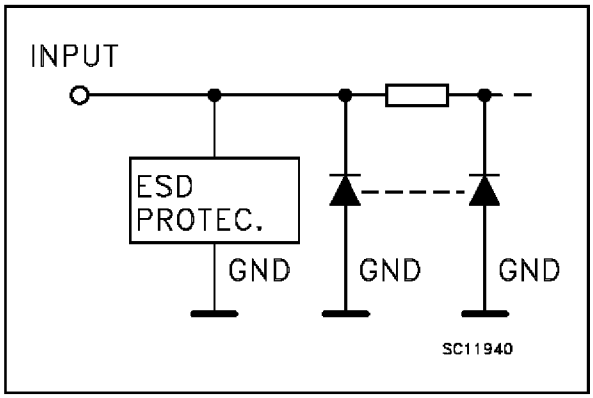
Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 19	$\overline{G1}$, $\overline{G2}$	Output Enable Input
2, 3, 4, 5, 6, 7, 8, 9	A1 to A8	Data Inputs
18, 17, 16, 15, 14, 13, 12, 11	Y1 to Y8	Data Outputs
10	GND	Ground (0V)
20	V_{CC}	Positive Supply Voltage

TRUTH TABLE

INPUT			OUTPUT
$\overline{G1}$	$\overline{G2}$	An	Yn
H	X	X	Z
X	H	X	Z
L	L	H	H
L	L	L	L

X: "H" or "L"
Z: High impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7.0	V
V_I	DC Input Voltage	-0.5 to +7.0	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	-20	mA
I_{OK}	DC Output Diode Current	±20	mA
I_O	DC Output Current	±25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	±75	mA
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	2.0 to 5.5	V
V_I	Input Voltage	0 to 5.5	V
V_O	Output Voltage	0 to V_{CC}	V
T_{op}	Operating Temperature	-40 to +85	°C
dt/dv	Input Rise and Fall Time (see note 1) (V_{CC} = 3.3 ± 0.3V) (V_{CC} = 5.0 ± 0.5V)	0 to 100 0 to 20	ns/V ns/V

1) V_{IN} from 30% to 70% of V_{CC}

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value					Unit
		V_{CC} (V)		T_A = 25 °C			-40 to 85 °C		
				Min.	Typ.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0		1.5			1.5		V
		3.0 to 5.5		0.7V_{CC}			0.7V_{CC}		
V_{IL}	Low Level Input Voltage	2.0				0.5		0.5	V
		3.0 to 5.5				0.3V_{CC}		0.3V_{CC}	
V_{OH}	High Level Output Voltage	2.0	I_O=-50 µA	1.9	2.0		1.9		V
		3.0	I_O=-50 µA	2.9	3.0		2.9		
		4.5	I_O=-50 µA	4.4	4.5		4.4		
		3.0	I_O=-4 mA	2.58			2.48		
		4.5	I_O=-8 mA	3.94			3.8		
V_{OL}	Low Level Output Voltage	2.0	I_O=50 µA		0.0	0.1		0.1	V
		3.0	I_O=50 µA		0.0	0.1		0.1	
		4.5	I_O=50 µA		0.0	0.1		0.1	
		3.0	I_O=4 mA			0.36		0.44	
		4.5	I_O=8 mA			0.36		0.44	
I_{OZ}	High Impedance Output Leakage Current	5.5	V_I = V_{IH} or V_{IL} V_O = V_{CC} or GND			±0.25		±2.5	µA
I_I	Input Leakage Current	0 to 5.5	V_I = 5.5V or GND			±0.1		±1.0	µA
I_{CC}	Quiescent Supply Current	5.5	V_I = V_{CC} or GND			4		40	µA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f =3 ns)

Symbol	Parameter	Test Condition			Value					Unit
		V_{CC} (V)	C_L (pF)		T_A = 25 °C			-40 to 85 °C		
					Min.	Typ.	Max.	Min.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time	3.3(*)	15			5.0	7.0	1.0	8.5	ns
		3.3(*)	50			7.5	10.5	1.0	12.0	
		5.0(**)	15			3.5	5.0	1.0	6.0	
		5.0(**)	50			5.0	7.0	1.0	8.0	
t_{PZL} t_{PZH}	Output Enable Time	3.3(*)	15	R_L = 1KΩ		6.8	10.5	1.0	12.5	ns
		3.3(*)	50	R_L = 1KΩ		9.3	14.0	1.0	16.0	
		5.0(**)	15	R_L = 1KΩ		4.7	7.2	1.0	8.5	
		5.0(**)	50	R_L = 1KΩ		6.2	9.2	1.0	10.5	
t_{PLZ} t_{PHZ}	Output Disable Time	3.3(*)	50	R_L = 1KΩ		11.2	15.4	1.0	17.5	ns
		5.0(**)	50	R_L = 1KΩ		6.0	8.8	1.0	10.0	
t_{OSLH} t_{OSHL}	Output to Output Skew Time (note 1)	3.3(*)	50				1.5		1.5	ns
		5.0(**)	50				1.0		1.0	

(*) Voltage range is 3.3V ± 0.3V
(**) Voltage range is 5V ± 0.5V
Note 1: Parameter guaranteed by design. $t_{soLH} = |t_{pLHm} - t_{pLHn}|$, $t_{soHL} = |t_{pHLm} - t_{pHLn}|$

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions	Value					Unit
			T_A = 25 °C			-40 to 85 °C		
			Min.	Typ.	Max.	Min.	Max.	
C_{IN}	Input Capacitance			4	10		10	pF
C_{OUT}	Output Capacitance			6				pF
C_{PD}	Power Dissipation Capacitance (note 1)			18				pF

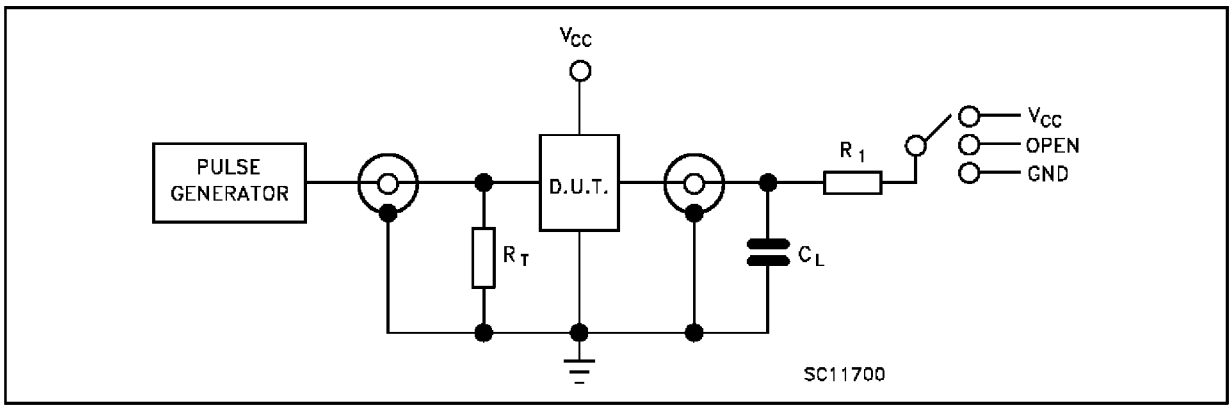
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/8$ (per Circuit)

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value					Unit
		V_{CC} (V)		T_A = 25 °C			-40 to 85 °C		
				Min.	Typ.	Max.	Min.	Max.	
V_{OLP}	Dynamic Low Voltage Quiet Output (note 1, 2)	5.0	C_L = 50 pF		0.6	0.9			V
V_{OLV}				-0.9	-0.6				
V_{IHD}	Dynamic High Voltage Input (note 1, 3)	5.0		3.5					
V_{ILD}	Dynamic Low Voltage Input (note 1, 3)	5.0				1.5			

1) Worst case package.
2) Max number of outputs defined as (n). Data inputs are driven 0V to 5.0V, (n -1) outputs switching and one output at GND.
3) Max number of data inputs (n) switching. (n-1) switching 0V to 5.0V. Inputs under test switching: 5.0V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f=1MHz.

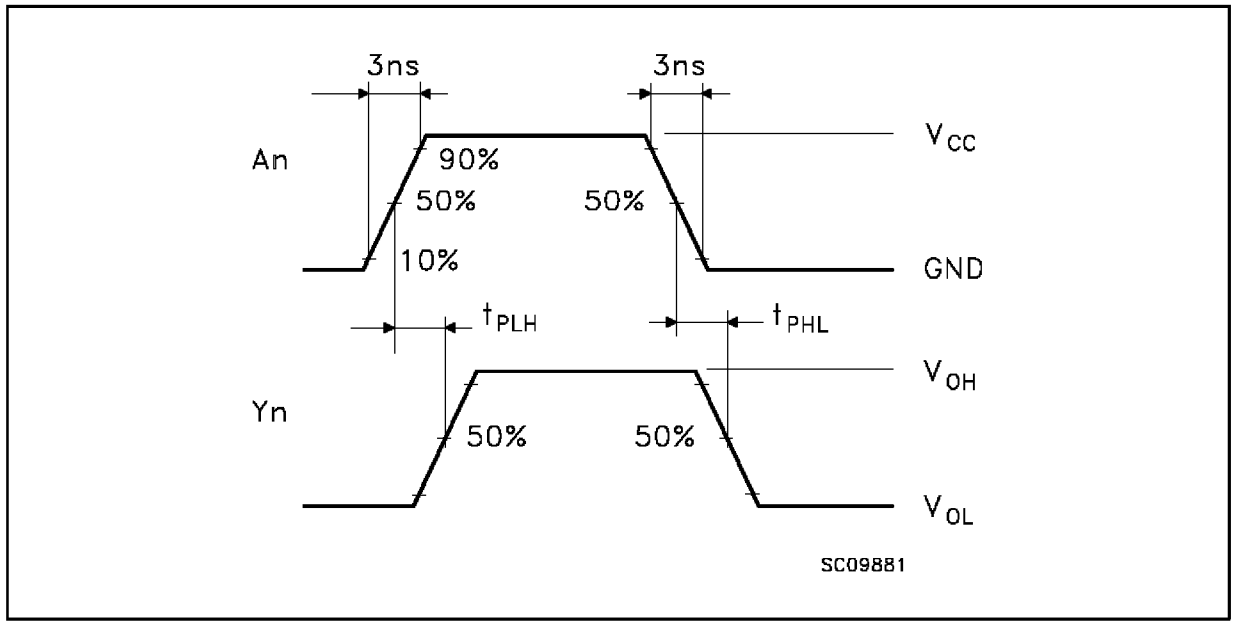
TEST CIRCUIT



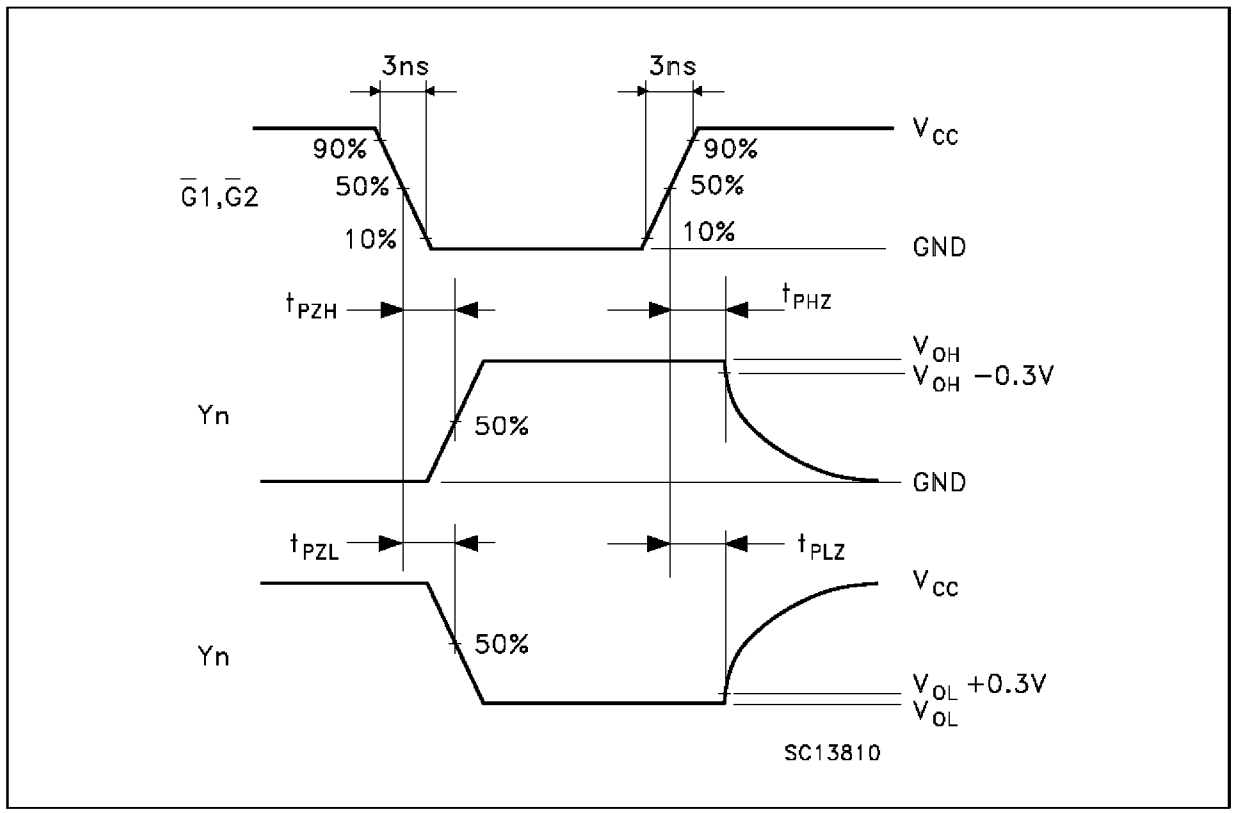
TEST	SWITCH
t_{PLH}, t_{PHL}	Open
t_{PZL}, t_{PLZ}	V_{CC}
t_{PZH}, t_{PHZ}	GND

C_L = 15/50 pF or equivalent (includes jig and probe capacitance)
$R_L = R_1$ = 1KΩ or equivalent
$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM 1: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)

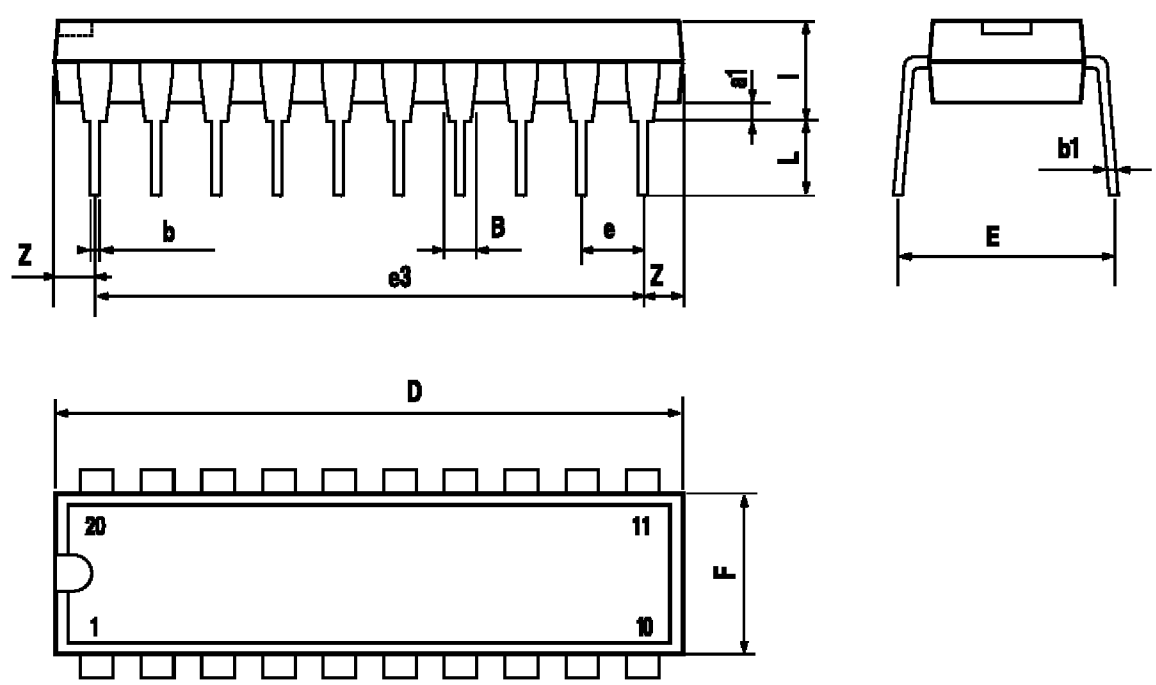


WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIME (f=1MHz; 50% duty cycle)



Plastic DIP-20 (0.25) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.254			0.010		
B	1.39		1.65	0.055		0.065
b		0.45			0.018	
b1		0.25			0.010	
D			25.4			1.000
E		8.5			0.335	
e		2.54			0.100	
e3		22.86			0.900	
F			7.1			0.280
I			3.93			0.155
L		3.3			0.130	
Z			1.34			0.053



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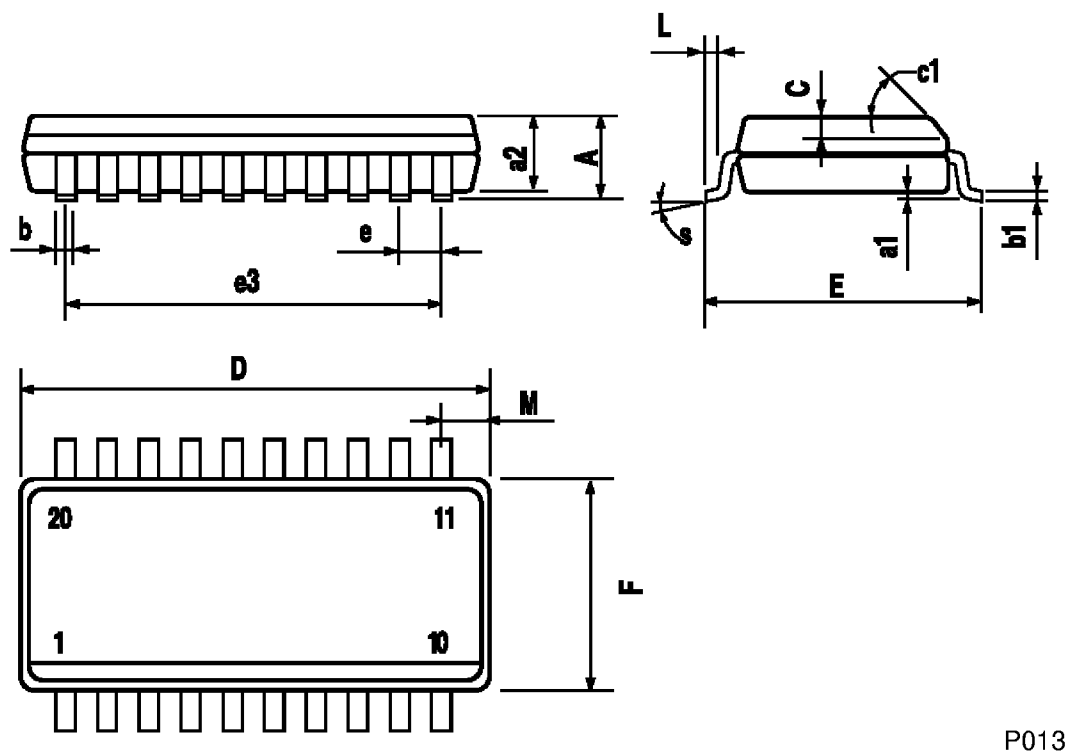
SO-20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.10		0.20	0.004		0.007
a2			2.45			0.096
b	0.35		0.49	0.013		0.019
b1	0.23		0.32	0.009		0.012
C		0.50			0.020	
c1	45 (typ.)					
D	12.60		13.00	0.496		0.512
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.299
L	0.50		1.27	0.19		0.050
M			0.75			0.029
S	8 (max.)					



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